

## **New 12.5V High Power MOSFET Modules for Commercial 2-way Radios**

**Ratingen, 13. August 2010** - Mitsubishi Electric is introducing two new 12.5V high power metal oxide semiconductor field effect transistor (MOSFET) devices. The two discrete devices, RD70HUF2 and RD35HUF2, are designed for use as high frequency power amplifiers in 2-way commercial radios operating at 25W and 50W respectively. Both models are available in VHF and UHF bands and compatible with/conform to surface mount technology (SMT) requirements.

The two new devices both feature high output powers and high efficiency. The RD70HUF2 has an output power of 75W at UHF and 84W at VHF and is optimized for 50W class radios. The RD35HUF2 offers an output power of 43W at UHF and 45W at VHF and is optimized for 25W class radios. The high drain efficiency, (the rate of electricity converted to RF power by amplifiers) of at least 60% at UHF and 70% at VHF for both devices will enable the next generation of commercial radios to offer a lower power consumptions than at present.

The RD70HUF2 and RD35HUF2 both conform to SMT standards, available in leadless plastic molded packages, suitable for use in a reflow soldering process. Furthermore, devices are shipped in tape and reel packaging and so are suitable for use with SMT placement equipment. Both devices use a new cost optimized package structure with low thermal resistance.

Commercial 2-way radios are widely used in many application fields like police departments and fire services, in Taxis, at airports and at event venues. They therefore require a rugged structure and reliable wireless communication capability with a high output power.

The new high power MOSFET modules are RoHS conform.

For more information please contact:

MITSUBISHI ELECTRIC EUROPE B.V.  
Semiconductor European Business Group  
Gothaer Straße 8  
D-40880 Ratingen

Phone +49 (21 02) 486-5270

semis.info@meg.mee.com  
www.mitsubishichips.eu